

# LZ1132BD/LZ1132BM/LZ1132BR

## 32-Unit High Voltage MOS IC

### Description

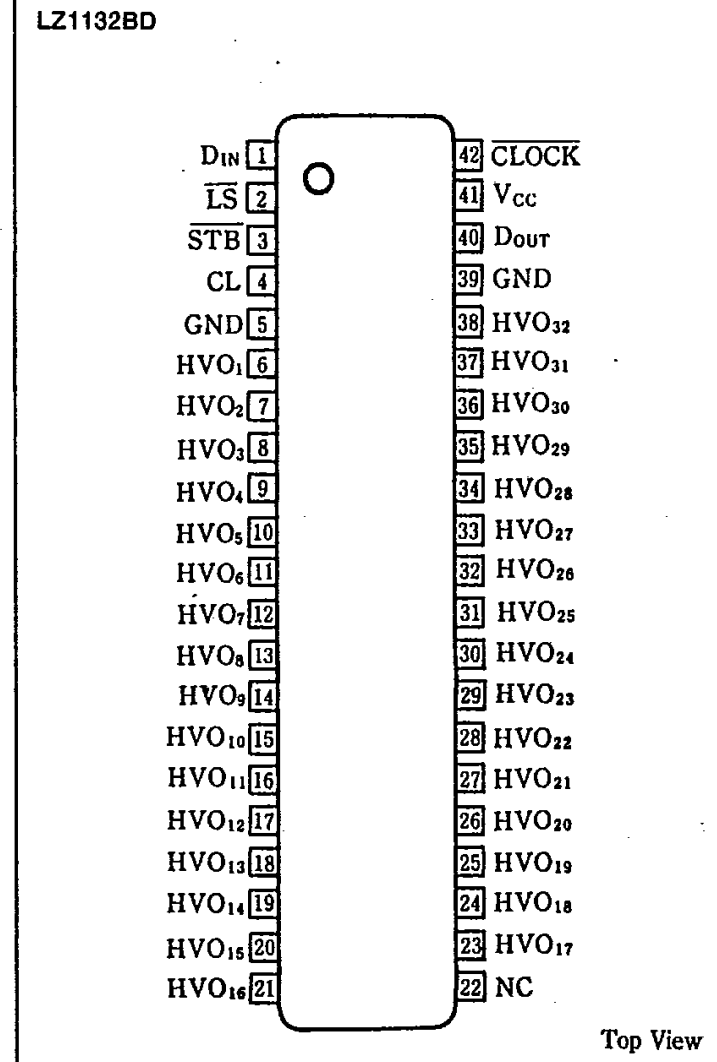
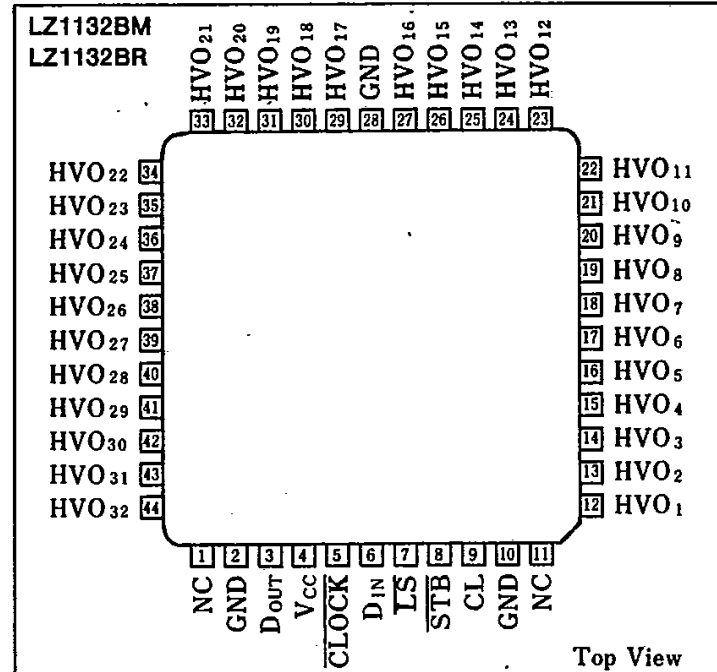
The LZ1132BD/LZ1132BM/LZ1132BR is a 300V 32-output-port monolithic IC fabricated using Sharp's advanced P-channel DMOS process. It can be used as a matrix driver for electroluminescent panels, plasma display panels, electrostatic printers.

### Features

1. High voltage output 300 (MIN.)
2. Output current 45mA (TYP.) at  $V_{HVO}=300V$
3. Internal 32-bit shift register circuit
4. Expandable circuit structure
5. High speed data transfer (clock frequency 4MHz)
6. Single power supply : -5V
7. DMOS process
8. 44-pin quad-flat package (LZ1132BM/LZ1132BR\*)  
42-pin dual-in-line package (LZ1132BD)

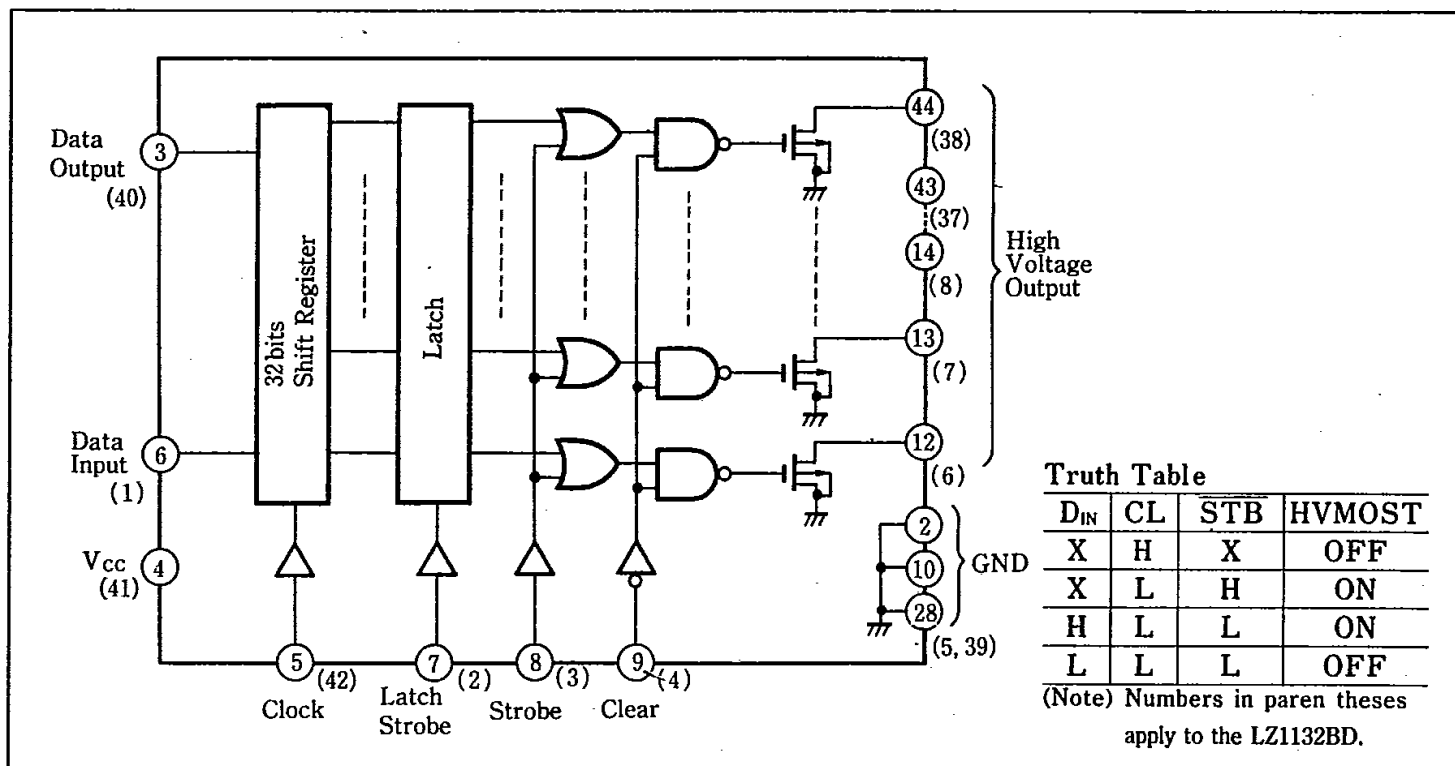
\* Reversed bend pin

### Pin Connections



T-43-24

## Block Diagram



## Absolute Maximum Ratings

(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit	Note
Supply voltage	V <sub>CC</sub>		-7 to +0.3	V	1
Input voltage	V <sub>IN</sub>	Applied to all input pins.	-7 to +0.3	V	1
Output voltage	V <sub>OUT</sub>	Applied to the data output	-7 to +0.3	V	1
	V <sub>HVO(ON)</sub>		-300 to +0.3	V	1,2
	V <sub>HVO(OFF)</sub>		-350 to +0.3	V	1,3
Power consumption	P <sub>D</sub>	T <sub>a</sub> ≤ 25°C	600	mW	
P <sub>D</sub> derating ratio	ΔP <sub>D</sub> /°C	T <sub>a</sub> > +25°C	5	mW/°C	
Operating temperature	T <sub>opr</sub>		-20 to +70	°C	
Storage temperature	T <sub>stg</sub>		-55 to +150	°C	

Note 1: The maximum applicable voltage on any pin with respect to GND.

Note 2: The maximum applicable voltage when HV MOST is ON. D (duty cycle) = 0.1%, ON time = 10 μs

Note 3: The maximum applicable voltage when HV MOST is OFF.

## DC Characteristics

### (1) HV MOST Characteristics

(V<sub>CC</sub> = -5V ± 10%)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Note
ON-state resistance	R <sub>ON</sub>	HV MOST "ON" I <sub>HVO</sub> = -1mA, T <sub>a</sub> = 25°C		1.0	1.3	Ω	
Output current	I <sub>HVO</sub>	HV MOST "ON" V <sub>HVO</sub> = -300V, T <sub>a</sub> = 25°C	-40	-45		mA	1
Output leakage current	I <sub>L</sub>	HV MOST "OFF" V <sub>HVO</sub> = -300V, T <sub>a</sub> = -20 to +70°C			10	μA	2
Total output leakage current	I <sub>TL</sub>	HV MOST "OFF" V <sub>HVO</sub> = -300V, T <sub>a</sub> = -20 to 70°C			30	μA	3

Note 1: Duty cycle = 0.1%, ON time = 10 μs

Note 2: Value for each HV MOST output pin.

Note 3: Sum of total output leakage current.

## (2) Logic Section Characteristics

 $(V_{CC}=5V \pm 10\%, T_a = -20 \text{ to } +70^\circ\text{C})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage	$I_{CC}$	$V_{IN}=0V$		-8	-16	mA
Input "High" voltage	$V_{IH}$		-0.8		0.3	V
Input "Low" voltage	$V_{IL}$		$V_{CC}$		-2.4	V
Output "High" voltage	$V_{OH}$	$I_{OH} = -0.2\text{mA}$ ; applied to $\overline{D_{OUT}}$	-0.5			V
Output "Low" voltage	$V_{OL}$	$I_{OL} = 1.6\text{mA}$ ; applied to $\overline{D_{OUT}}$			-2.5	V
Input leakage current	$I_{IL}$	$V_{IN}=0V \text{ to } V_{CC}$			10	$\mu\text{A}$

## AC Characteristics

 $(V_{CC}=5V \pm 10\%, T_a = -20 \text{ to } +70^\circ\text{C})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Note
Clock frequency	$f_{\phi}$				4	MHz	
Clock pulse width	$t_{\phi}, \overline{t_{\phi}}$		125			ns	
$\overline{D_{IN}}$ setup time	$t_{DS}$		60			ns	
$\overline{D_{IN}}$ hold time	$t_{DH}$		60			ns	
LS pulse width	$t_{LP}$		150			ns	
Clock to LS delay	$t_{CL}$		0			ns	
LS to clock delay	$t_{LC}$		0			ns	
$\overline{D_{OUT}}$ delay	$t_{PD}$	$C_L(D_{OUT})=30\text{pF}$			250	ns	
LS to STB delay	$t_{LSB}$		0			ns	
LS to $\overline{CL}$ delay	$t_{LCL}$		0			ns	
STB pulse width	$t_{SP}$		1			$\mu\text{s}$	
$\overline{CL}$ pulse width	$t_{CLP}$		1			$\mu\text{s}$	
HVO fall time	$t_{PL}$	$C_L(HVO)=900\text{pF}, R_L=20\text{k}\Omega$			60	$\mu\text{s}$	
HVO rise time	$t_{PH}$	$C_L(HVO)=900\text{pF}, R_L=20\text{k}\Omega$			15	$\mu\text{s}$	1

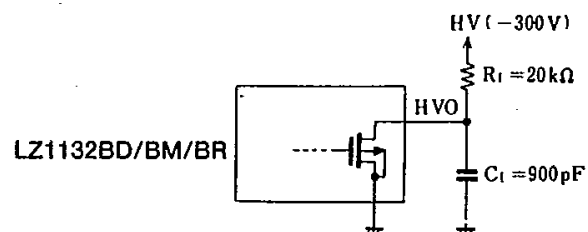
Note 1: Output delay time varies depending on load condition.

## Test conditions

Input rise/fall time: 20 ns

Time measurement level: 50%

HVO output load conditions (figure at right).

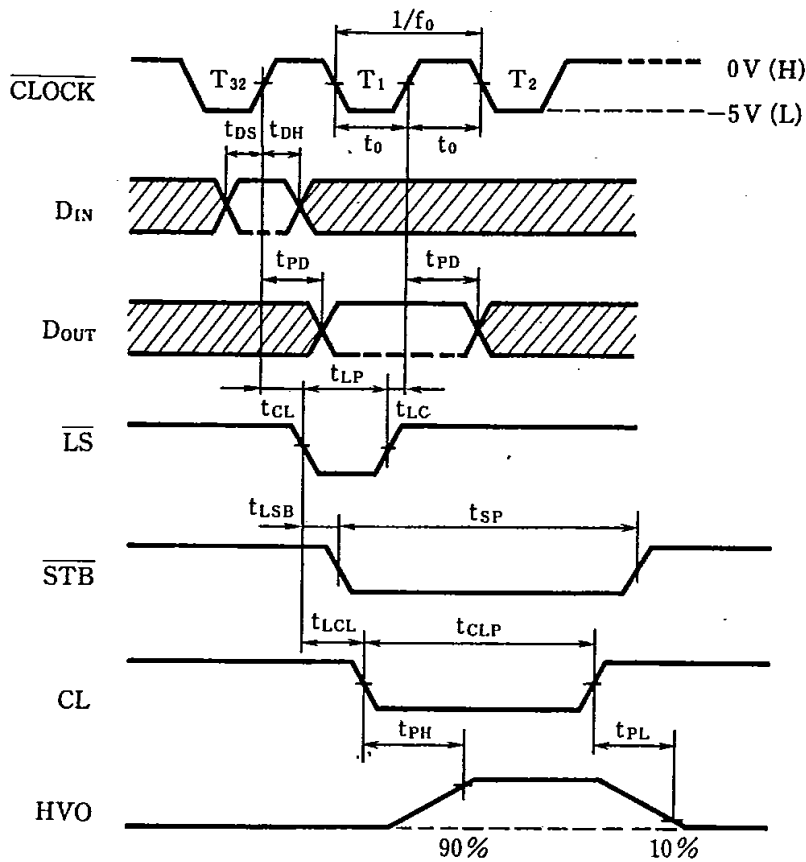
 $(V_{CC}=0V, f=1\text{MHz}, T_a=25^\circ\text{C})$ 

## Capacitance

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	$C_{IN}$	$V_{IN}=0V$		6	10	pF
Output capacitance	$C_{HVO}$	$V_{HVO}=0V$		17	30	pF

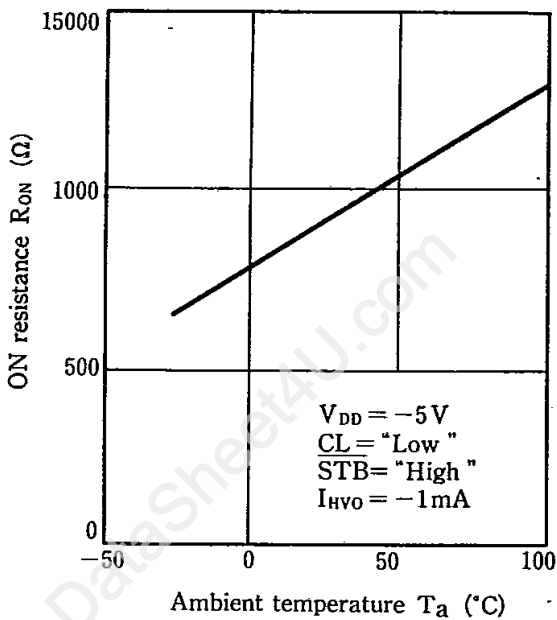
All pins except pin being measurement are connected to GND.

AC Timing Diagram

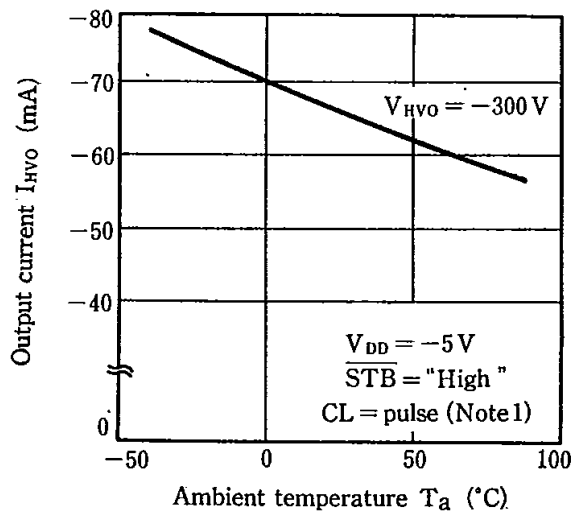


Electrical Characteristic Curve

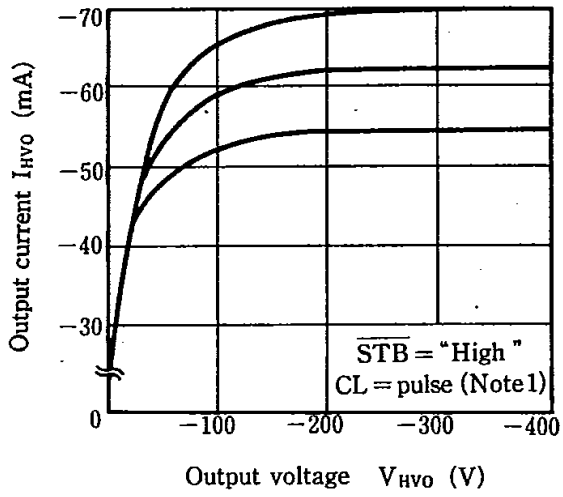
ON resistance vs. Ambient temperature



Output current vs. Ambient temperature



Output current vs. Output voltage



Note 1 : Apply below pulse to the CL.

